# UNISONIC TECHNOLOGIES CO., LTD

3NM60 **Preliminary** Power MOSFET

# 3.0A, 600V N-CHANNEL SUPER-JUNCTION MOSFET

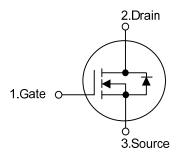
#### **DESCRIPTION**

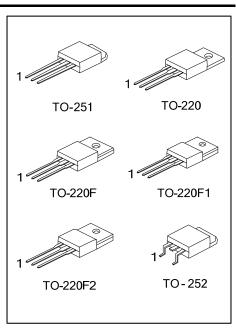
The UTC 3NM60 is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

#### **FEATURES**

- \*  $R_{DS(ON)}$  < 1.86 $\Omega$  @  $V_{GS}$  = 10 V,  $I_{D}$  = 1.5 A
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

#### **SYMBOL**

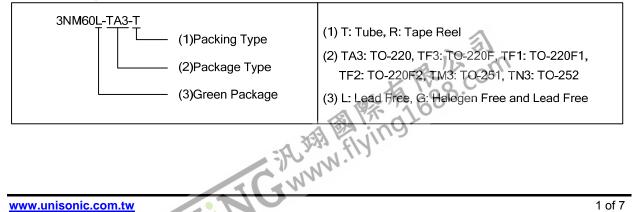




# **ORDERING INFORMATION**

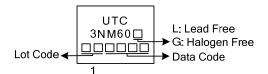
Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
3NM60L-TA3-T	3NM60G-TA3-T	TO-220	G	D	S	Tube	
3NM60L-TF1-T	3NM60G-TF1-T	TO-220F1	G	D	S	Tube	
3NM60L-TF2-T	3NM60G-TF2-T	TO-220F2	G	D	S	Tube	
3NM60L-TF3-T	3NM60G-TF3-T	TO-220F	G	D	S	Tube	
3NM60L-TM3-T	3NM60G-TM3-T	TO-251	G	D	S	Tube	
3NM60L-TN3-R	3NM60G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



www.unisonic.com.tw 1 of 7

#### **MARKING**





# ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub> = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	600	V
Gate-Source Voltage		$V_{GSS}$	±30	V
Continuous Drain Current		$I_{D}$	3.0	Α
Pulsed Drain Current (Note 2)		$I_{DM}$	12	Α
Avalanche Current (Note 2)		$I_{AR}$	1.2	Α
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	104	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	5.0	V/ns
Power Dissipation	TO-220		75	W
	TO-220F/TO-220F1	В	34	W
	TO-220F2	$P_D$	35	W
	TO-251/TO-252		50	W
Junction Temperature		$T_J$	+150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L=144mH,  $I_{AS}$ =1.2A,  $V_{DD}$ =50V,  $R_{G}$ =25  $\Omega$ , Starting  $T_{J}$  = 25°C
- 4.  $I_{SD} \le 3.0A$ , di/dt $\le 200A/\mu s$ ,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J = 25$ °C

# **■ THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT	
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	$\theta_{JA}$	62.5	°C/W	
	TO-251/TO-252		110		
Junction to Case	TO-220	θлс	1.67		
	TO-220F/TO-220F1		3.68	°C/W	
	TO-220F2		3.58		
	TO-251/TO-252		2.5		



# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> =25°C, unless otherwise specified)

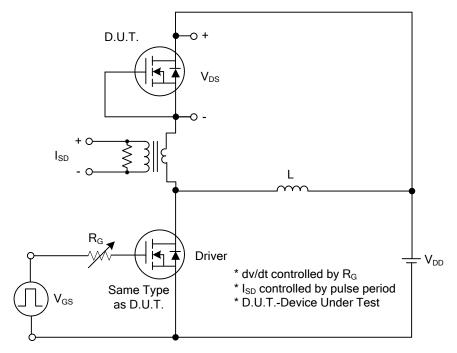
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =250μA	600			V	
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =600 V, V <sub>GS</sub> =0V			10	μA	
Gate-Source Leakage Current	Forward	,	V <sub>GS</sub> =+30 V, V <sub>DS</sub> =0V			+100	nA	
	Reverse	$I_{GSS}$	V <sub>GS</sub> =-30 V, V <sub>DS</sub> =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	2.5		4.5	V	
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.5A			1.86	Ω	
DYNAMIC CHARACTERISTICS				-	=.	a		
Input Capacitance		C <sub>ISS</sub>			222		pF	
Output Capacitance		Coss	$V_{GS}$ =0V, $V_{DS}$ =25V, f=1MHz		148		pF	
Reverse Transfer Capacitance		C <sub>RSS</sub>			15		pF	
SWITCHING CHARACTERISTICS								
Total Gate Charge (Note 1)		$Q_G$	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.3A,		30		nC	
Gate to Source Charge		$Q_GS$	$I_{G}=100\mu A$ (Note 1, 2)		3.6		nC	
Gate to Drain Charge		$Q_{DD}$	I <sub>G</sub> -100μA (Note 1, 2)		6.4		nC	
Turn-ON Delay Time (Note 1)		t <sub>D(ON)</sub>	$V_{DD}$ =30V, $V_{GS}$ =10V, $I_{D}$ =0.5A, $R_{G}$ =25 $\Omega$ (Note 1, 2)		38		ns	
Rise Time		t <sub>R</sub>			45		ns	
Turn-OFF Delay Time		t <sub>D(OFF)</sub>			90		ns	
Fall-Time		t <sub>F</sub>			31		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous (	Current	Is				3.0	Α	
Maximum Body-Diode Pulsed Curre	ent	I <sub>SM</sub>				8.0	Α	
Drain-Source Diode Forward Voltage	je (Note 1)	$V_{SD}$	I <sub>S</sub> =3.0 A, V <sub>GS</sub> =0 V			1.4	V	
Body Diode Reverse Recovery Time (Note 1)		t <sub>rr</sub>	I <sub>S</sub> =3.0 A, V <sub>GS</sub> =0 V		210		ns	
Body Diode Reverse Recovery Charge		Qrr	dI <sub>F</sub> /dt=100A/µs		1.4		μC	

Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle≤2%.

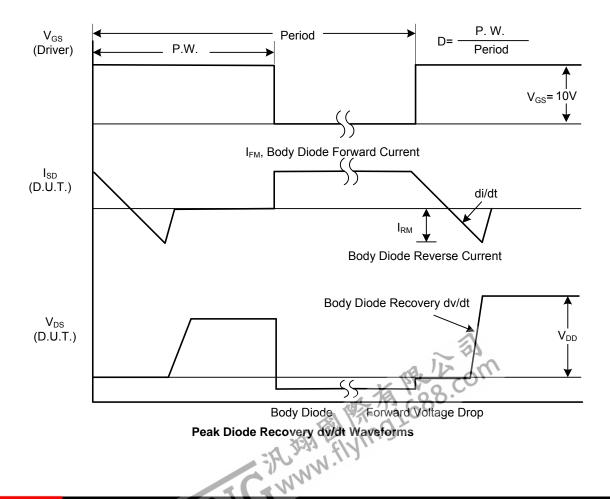


<sup>2.</sup> Essentially independent of operating temperature.

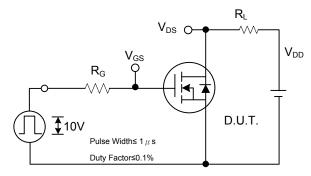
#### ■ TEST CIRCUITS AND WAVEFORMS



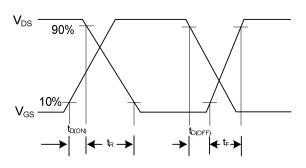
Peak Diode Recovery dv/dt Test Circuit



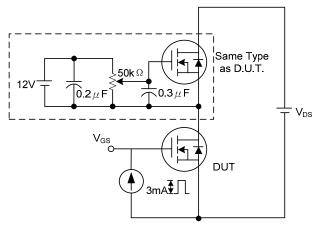
# **TEST CIRCUITS AND WAVEFORMS (Cont.)**



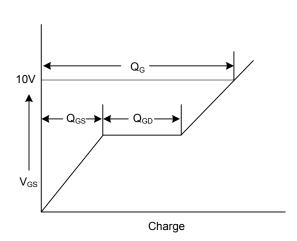
**Switching Test Circuit** 



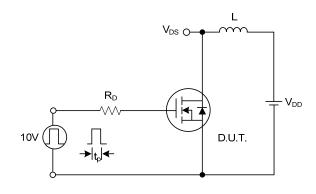
**Switching Waveforms** 



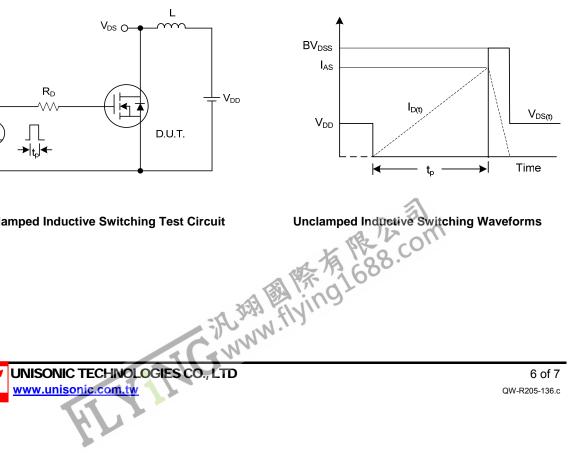
**Gate Charge Test Circuit** 



**Gate Charge Waveform** 



**Unclamped Inductive Switching Test Circuit** 



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

